

SOT-23 Plastic-Encapsulate Transistors

B772 TRANSISTOR(PNP)

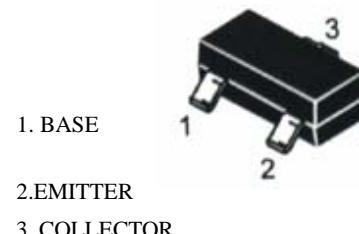
## FEATURES

- Complimentary to D882
- Collector Current:  $I_C = -1.5A$

MARKING: B772

MAXIMUM RATINGS(TA=25°C unless otherwise noted)

## SOT-23



Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-40	V
VCEO	Collector-Emitter Voltage	-30	V
VEBO	Emitter-Base Voltage	-6	V
IC	Collector Current-Continuous	-1.5	A
PC	Coueator Power Dissipature	-0.3	W
TJ	Junction Temperature	150	°C
Tatg	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CB0	$I_C = -1mA, I_E = 0$	-40			V
Collector-emittre breakdown' voltage	V(BR)CEO	$I_C = -1mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	V(BR)EBO	$I_C = -1mA, I_E = 0$	-6			V
Collector cut-off current	$I_{CB0}$	$V_{CB} = -40V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -30V, I_B = 0$			-0.5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current gain	HFE	$V_{CE} = -5V, I_C = -1mA$	60		400	
Collector-emittre saturation voltage	VCE(sat)	$I_C = -800mA, I_B = -80mA$			-0.5	V
Base-emittre saturation voltage	VBE(sat)	$I_C = -800mA, I_B = -80mA$			-1.2	V
Gain Bandwidth Product	Ft	$V_{CE} = -10V, I_C = -50mA, f = 30MHz$	100			MHz
Collector output capacitance	Cob	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	pF